N-Channel 30-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

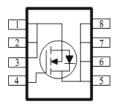
Typical Applications:

- DC/DC Conversion
- Power Routing
- Motor Drives

| PRODUCT SUMMARY | | | | |
|---------------------|---------------------------|--------------------|--|--|
| V _{DS} (V) | $r_{DS(on)}(m\Omega)$ | I _D (A) | | |
| 30 | 1 @ V _{GS} = 10V | 200° | | |
| 30 | $1.3 @ V_{GS} = 4.5V$ | 200 | | |







| ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED) | | | | | | | |
|---|----------------------|----------------|------------------|----|--|--|--|
| Parameter | Symbol | Limit | Units | | | | |
| Drain-Source Voltage | | | 30 | V | | | |
| Gate-Source Voltage | V_{GS} | ±20 | V | | | | |
| | T _C =25°C | | 200 ^c | A | | | |
| Continuous Drain Current | T _C =70°C | l _D | 200 ^c | | | | |
| Continuous Diam Guiterit | T _A =25°C | | 68 ^a | | | | |
| | T _A =70°C | | 55 ^a | | | | |
| Pulsed Drain Current ^b | I _{DM} | 450 | 1 | | | | |
| Continuous Source Current (Diode Conduction) ^a | | Is | 10 | | | | |
| | T _C =25°C | | 156 | W | | | |
| Power Dissipation | T _C =70°C | P_{D} | 100 | | | | |
| Prower Dissipation | T _A =25°C | ' D | 6.9 ^a | VV | | | |
| | T _A =70°C | | 4.4 ^a | | | | |
| Operating Junction and Storage Temperature Range | | T_J,T_stg | -55 to 150 | °C | | | |

| THERMAL RESISTANCE RATINGS | | | | | | | | |
|--|--------------|-----------------|-------|------|--|--|--|--|
| Parameter | Symbol | Maximum | Units | | | | | |
| Maximum Junction-to-Ambient ^a | t <= 10 sec | $R_{\theta JA}$ | 18 | °C/W | | | | |
| IMAXIIIIUIII JUIICUOII-to-AIIIbleIIt | Steady State | IXOJA | 50 | | | | | |
| Maximum Junction-to-Case | Steady State | $R_{\theta JC}$ | 0.8 | | | | | |

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature
- c. Package limited

Electrical Characteristics

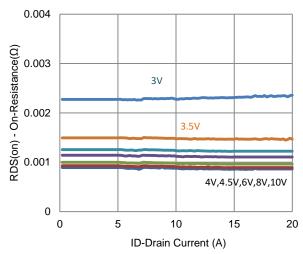
| Parameter | Symbol | Test Conditions | Min | Тур | Max | Unit | | |
|---|---------------------|--|-----|------|------|-------|--|--|
| Static | | | | | | | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$ | 1 | | | V | | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ±100 | nA | | |
| Zero Gate Voltage Drain Current | lass | $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$ | | | 1 | uA | | |
| Zero Gate Voltage Brain Guirent | I _{DSS} | $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ | | | 10 | | | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$ | 80 | | | Α | | |
| Drain Source On Besistance a | r | $V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$ | | | 1 | mΩ | | |
| Drain-Source On-Resistance ^a | r _{DS(on)} | $V_{GS} = 4.5 \text{ V}, I_D = 16 \text{ A}$ | | | 1.3 | 11122 | | |
| Forward Transconductance ^a | g _{fs} | $V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$ | | 150 | | S | | |
| Diode Forward Voltage ^a | V_{SD} | $I_{S} = 5 \text{ A}, V_{GS} = 0 \text{ V}$ | | 0.69 | | V | | |
| | | Dynamic ^b | | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$ | | 102 | | | | |
| Gate-Source Charge | Q_{gs} | $I_{D} = 20 \text{ A}$ | | 24 | | nC | | |
| Gate-Drain Charge | Q_gd | 1D = 20 A | | 37 | | | | |
| Turn-On Delay Time | t _{d(on)} | $V_{DS} = 15 \text{ V}, R_1 = 0.8 \Omega,$ | | 26 | | | | |
| Rise Time | t _r | $V_{DS} = 13 \text{ V}, \text{ K}_{L} = 0.6 \Omega,$ $I_{D} = 20 \text{ A},$ | | 51 | | ne | | |
| Turn-Off Delay Time | $t_{d(off)}$ | $V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$ | | 299 | | ns | | |
| Fall Time | t _f | V GEN = 10 V, 1 (GEN = 0.22 | | 129 | | | | |
| Input Capacitance | C _{iss} | | | 7882 | | | | |
| Output Capacitance | C _{oss} | $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$ | | 1456 | | pF | | |
| Reverse Transfer Capacitance | C_{rss} | | | 1387 | | | | |

Notes

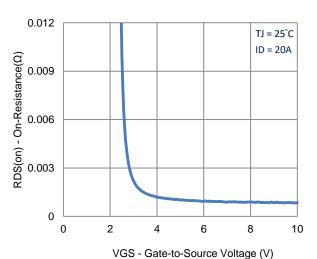
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing.

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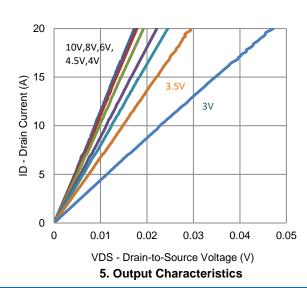
Typical Electrical Characteristics

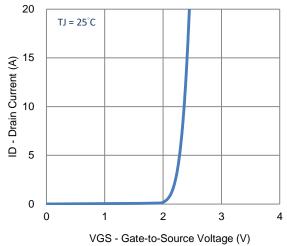


1. On-Resistance vs. Drain Current

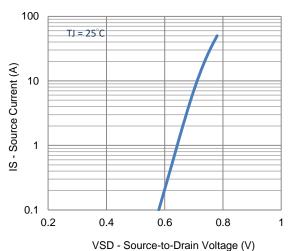


3. On-Resistance vs. Gate-to-Source Voltage

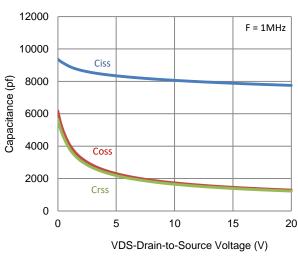




2. Transfer Characteristics

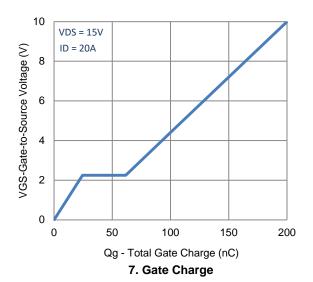


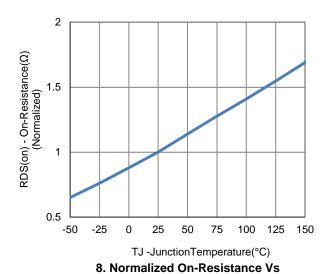
4. Drain-to-Source Forward Voltage



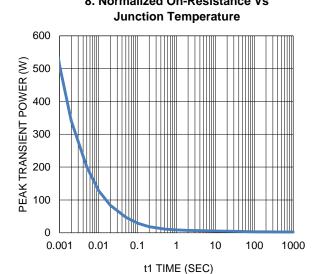
6. Capacitance

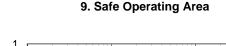
Typical Electrical Characteristics



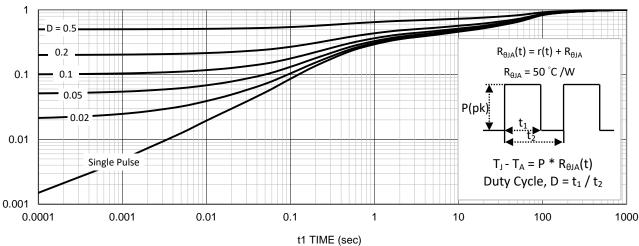


1000
100 us
100 us
100 us
100 us
100 ms
100 ms
100 ms
100 ms
100 sec
1



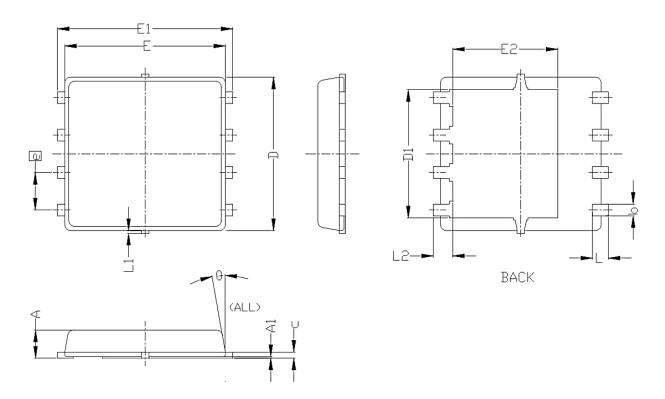






11. Normalized Thermal Transient Junction to Ambient

Package Information



| SYMBOLS | DIMENSIONS IN MILLIMETERS | | | DIMENSIONS IN INCHES | | | |
|---------|---------------------------|------|-------|----------------------|-------|-------|--|
| STMBULS | MIN | NOM | MAX | MIN | NOM | MAX | |
| A | 0.85 | 0.95 | 1.00 | 0.033 | 0.037 | 0.039 | |
| A1 | 0.00 | | 0.05 | 0.000 | | 0.002 | |
| b | 0.30 | 0.40 | 0.50 | 0.012 | 0.016 | 0.020 | |
| С | 0. 15 | 0.20 | 0. 25 | 0.006 | 0.008 | 0.010 | |
| D | 5. 20 BSC | | | 0. 205 BSC | | | |
| D1 | 4. 35 BSC | | | 0. 171 BSC | | | |
| | | | | | | | |
| E | 5, 55 BSC | | | 0, 219 BSC | | | |
| E1 | 6. 05 BSC | | | 0. 238 BSC | | | |
| E2 | 3. 62 BSC | | | 0. 143 BSC | | | |
| e | 1. 27 BSC | | | 0.050 BSC | | | |
| L | 0.45 | 0.55 | 0.65 | 0.018 | 0.022 | 0.026 | |
| Ll | 0 | | 0.15 | 0 | | 0.006 | |
| L2 | 0.68 REF | | | 0. 027 REF | | | |
| θ | 0° | | 10° | 0° | | 10° | |